ESD Protection Diode

Low Capacitance ESD Protection for LVDS Interfaces

The ESDR7534 surge protection is designed to protect high speed data lines from ESD, EFT, and lightning.

Features

- Low Capacitance (2 pF Maximum Between I/O Lines and GND)
- Protection for the Following IEC Standards: IEC 61000–4–2 (ESD) Level 4 – ±30 kV (Contact); ±30 kV (Air)
- This is a Pb–Free Device

MAXIMUM RATINGS (T_J = 25° C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1)	P _{pk}	300	W
Maximum Peak Pulse Current 2/10 μ s @ T _A = 25°C	I _{PP}	10	A
Operating Junction Temperature Range	Τ _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)	ΤL	260	°C
IEC 61000–4–2 Contact IEC 61000–4–2 Air ISO 10605 330 pF / 330 Ω Contact ISO 10605 330 pF / 2 kΩ Contact ISO 10605 150 pF / 2 kΩ Contact	ESD		kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. P_{pk} calculated. $P_{pk} = V_C \times I_{PP}$.

Table 1. PIN DESCRIPTIONS

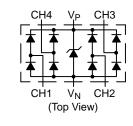
	4–Channel, 6–Lead SC70–6				
Pin	Name	Туре	Description		
1	CH1	I/O	ESD Channel		
2	V _N	GND	Negative Voltage Supply Rail		
3	CH2	I/O	ESD Channel		
4	CH3	I/O	ESD Channel		
5	VP	PWR	Positive Voltage Supply Rail		
6	CH4	I/O	ESD Channel		

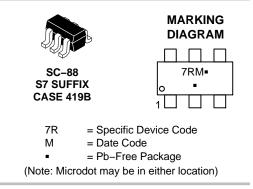


ON Semiconductor®

www.onsemi.com

PIN CONFIGURATION AND SCHEMATIC





ORDERING INFORMATION

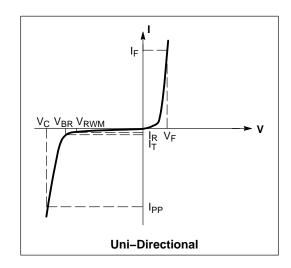
Device	Package	Shipping [†]
ESDR7534W1T2G	SC-88 (Pb-Free)	3,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

	,
Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ IPP
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V_{BR}	Breakdown Voltage @ I _T
Ι _Τ	Test Current
١ _F	Forward Current
V _F	Forward Voltage @ I _F
P _{pk}	Peak Power Dissipation
С	Capacitance @ $V_R = 0$ and f = 1.0 MHz



*See Application Note AND8308/D for detailed explanations of datasheet parameters.

Parameter Symbol Conditions		Min	Тур	Max	Unit	
Reverse Working Voltage	V _{RWM}	(Note 1)			5.0	V
Breakdown Voltage	V _{BR}	I _T = 1 mA, (Note 2)	6.0	8.0	9.5	V
Reverse Leakage Current	I _R	V _{RWM} = 5 V			3.0	μΑ
Forward Voltage	V _F	I _F = 100 mA			1.6	V
Clamping Voltage	V _C	I _{PP} = 10 A (2/10 μs Waveform)			30	V
Maximum Peak Pulse Current	I _{PP}	2/10 μs Waveform			10	А
Junction Capacitance	CJ	$V_R = 0 V$, f = 1 MHz between I/O Pins and GND		1.3	2.0	pF
Junction Capacitance	CJ	$V_R = 0 V$, f = 1 MHz between I/O Pins, V_P floating		0.7	1.0	pF

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

1. Surge protection devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.

2. $V_{\mbox{\scriptsize BR}}$ is measured at pulse test current $\mbox{\scriptsize I_T}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

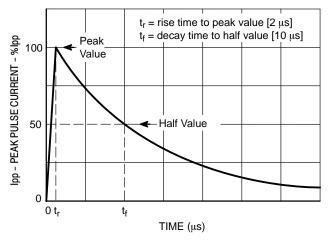
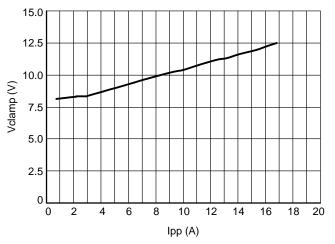
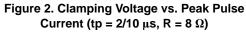


Figure 1. Exponential Decay Pulse Waveform





IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)	
1	2	7.5	4	2	
2	4	15	8	4	
3	6	22.5	12	6	
4	8	30	16	8	

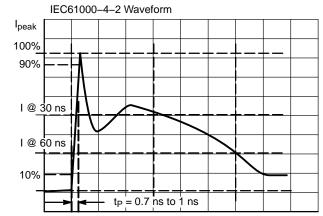


Figure 3. IEC61000-4-2 Spec

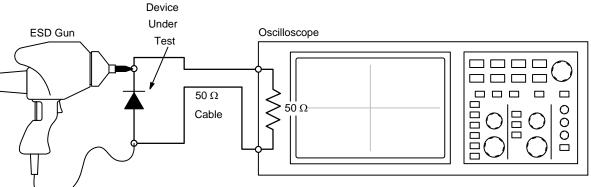


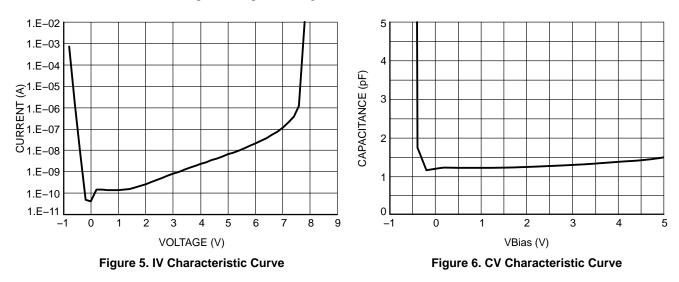
Figure 4. Diagram of ESD Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.



ESDR7534

APPLICATIONS INFORMATION

The new ESDR7534 is a low capacitance surge protection diode array designed to protect sensitive electronics such as communications systems, computers, and computer peripherals against damage due to ESD events or transient overvoltage conditions. Because of its low capacitance, it can be used in high speed I/O data lines. The integrated design of the ESDR7534 offers low capacitance steering diodes and an internal surge protection diode (V_P diode) integrated in a single package. If a transient condition occurs, the steering diodes will drive the transient to the positive rail of the power supply or to ground. The surge protection device protects the power line against overvoltage conditions to avoid damage to the power supply and any downstream components.

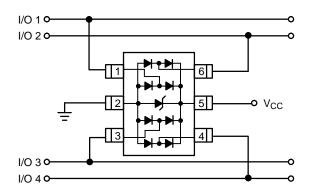
ESDR7534 Configuration Options

The ESDR7534 is able to protect up to four data lines against transient overvoltage conditions by driving them to a fixed reference point for clamping purposes. The steering diodes will be forward biased whenever the voltage on the protected line exceeds the reference voltage (V_f or V_{CC} + V_f). The diodes will force the transient current to bypass the sensitive circuit.

Data lines are connected at pins 1, 3, 4 and 6. The negative reference is connected at pin 2. This pin must be connected directly to ground by using a ground plane to minimize the PCB's ground inductance. It is very important to reduce the PCB trace lengths as much as possible to minimize parasitic inductances.

Option 1

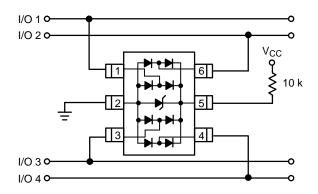
Protection of four data lines and the power supply using V_{CC} as reference.



For this configuration, connect pin 5 directly to the positive supply rail (V_{CC}), the data lines are referenced to the supply voltage. The V_P diode prevents overvoltage on the supply rail. Biasing of the steering diodes reduces their capacitance.

Option 2

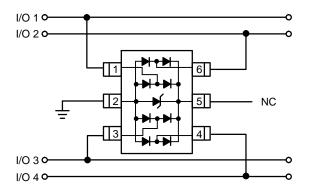
Protection of four data lines with bias and power supply isolation resistor.



The ESDR7534 can be isolated from the power supply by connecting a series resistor between pin 5 and V_{CC}. A 10 k Ω resistor is recommended for this application. This will maintain a bias on the V_P and steering diodes, reducing their capacitance.

Option 3

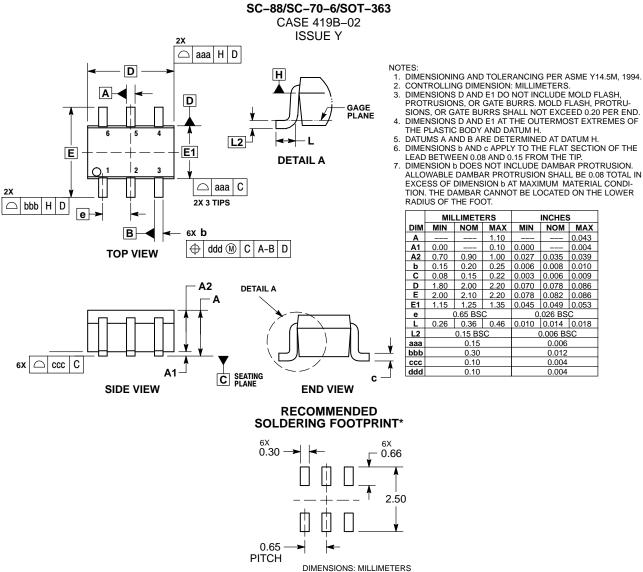
Protection of four data lines using the V_P diode as reference.



In applications lacking a positive supply reference or those cases in which a fully isolated power supply is required, the V_P can be used as the reference. For these applications, pin 5 is not connected. In this configuration, the steering diodes will conduct whenever the voltage on the protected line exceeds the V_{BR} of the I/O (CHX) pin.

ESDR7534

PACKAGE DIMENSIONS



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and 💷 are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdl/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typical" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

ON Semiconductor Website: www.onsemi.com Order Literature: http://www.onsemi.com/orderlit

Sales Representative

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

For additional information, please contact your local

ESDR7534/D

Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80 2.00		2.20	0.070	0.078	0.086
Е	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
CCC	0.10			0.004		

0.10

INCHES MIN NOM MAX

0.004